

# Jeong Woo Jeon

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Atomic layer deposition of SnSe thin films using Sn(N(CH <sub>3</sub> ) <sub>2</sub> ) <sub>4</sub> and Se(Si(CH <sub>3</sub> ) <sub>3</sub> ) <sub>2</sub> with NH <sub>3</sub> co-injection. Dalton Transactions, 2022, 51, 594-601.	3.3	2
2	Atomic layer deposition of chalcogenides for next-generation phase change memory. Journal of Materials Chemistry C, 2021, 9, 3708-3725.	5.5	23
3	Time-varying data processing with nonvolatile memristor-based temporal kernel. Nature Communications, 2021, 12, 5727.	12.8	42
4	Kernel Application of the Stacked Crossbar Array Composed of Self-Rectifying Resistive Switching Memory for Convolutional Neural Networks. Advanced Intelligent Systems, 2020, 2, 1900116.	6.1	11
5	Atomic Layer Deposition of SnTe Thin Film Using Sn(N(CH <sub>3</sub> ) <sub>2</sub> ) <sub>4</sub> and Te(Si(CH <sub>3</sub> ) <sub>3</sub> ) <sub>2</sub> with Ammonia Coinjection. Crystal Growth and Design, 2020, 20, 4649-4656.	3.0	5
6	Atomic Layer Deposition of Ge <sub>x</sub> Se <sub>1-x</sub> Thin Films for Endurable Ovonic Threshold Selectors with a Low Threshold Voltage. ACS Applied Materials & Interfaces, 2020, 12, 23110-23118.	8.0	19
7	Atomic Layer Deposition of Nanocrystalline-As-Deposited (GeTe) <sub>x</sub> (Sb <sub>2</sub> Te <sub>3</sub> ) <sub>1-x</sub> Films for Endurable Phase Change Memory. Chemistry of Materials, 2019, 31, 8752-8763.	6.7	15
8	Developing Precursor Chemistry for Atomic Layer Deposition of High-Density, Conformal GeTe Films for Phase-Change Memory. Chemistry of Materials, 2019, 31, 8663-8672.	6.7	12
9	Electroforming-Free Bipolar Resistive Switching in GeSe Thin Films with a Ti-Containing Electrode. ACS Applied Materials & Interfaces, 2019, 11, 38910-38920.	8.0	13
10	Fabrication of a Cone-Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. Advanced Functional Materials, 2019, 29, 1806278.	14.9	51